



TRISIL™ FOR TELECOM EQUIPMENT PROTECTION

FEATURES

- Bidirectional crowbar protection
- Voltage: range from 120V to 270V
- Low V_{BO} / V_R ratio
- Micro capacitance equal to 12pF @ 50V
- Low leakage current : $I_R = 2\mu A$ max
- Holding current: $I_H = 150$ mA min
- Repetitive peak pulse current :
- $I_{PP} = 80$ A (10/1000 μs)

MAIN APPLICATIONS

Any sensitive equipment requiring protection against lightning strikes and power crossing:

- Terminals (phone, fax, modem...) and central office equipment

DESCRIPTION

The SMP80MC is a series of micro capacitance transient surge arrestors designed for the protection of high debit rate communication equipment on CPE side. Its micro capacitance avoids any distortion of the signal and is compatible with digital transmission like ADSL2 and ADSL2+.

BENEFITS

Trisils are not subject to ageing and provide a fail safe mode in short circuit for a better protection. They are used to help equipment to meet main standards such as UL1950, IEC950 / CSA C22.2 and UL1459. They have UL94 V0 approved resin. SMB package is JEDEC registered (DO-214AA). Trisils comply with the following standards GR-1089 Core, ITU-T-K20/K21, VDE0433, VDE0878, IEC61000-4-5 and FCC part 68.

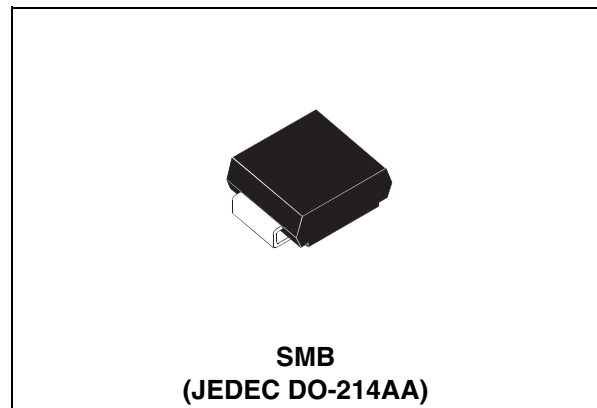


Table 1: Order Codes

Part Number	Marking
SMP80MC-120	TP12
SMP80MC-140	TP14
SMP80MC-160	TP16
SMP80MC-200	TP20
SMP80MC-230	TP23
SMP80MC-270	TP27

Figure 1: Schematic Diagram

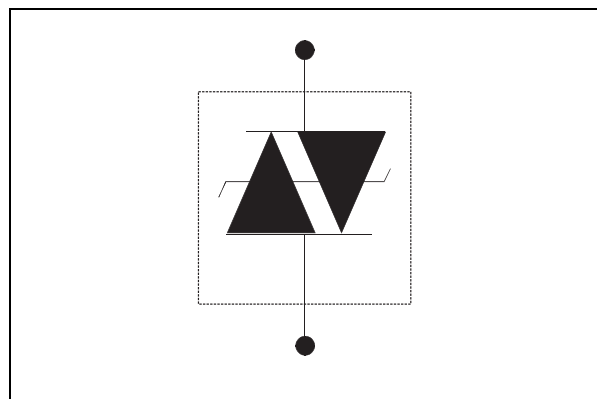


Table 2: In compliances with the following standards

STANDARD	Peak Surge Voltage (V)	Waveform Voltage	Required peak current (A)	Current waveform	Minimum serial resistor to meet standard (Ω)
GR-1089 Core First level	2500 1000	2/10 μ s 10/1000 μ s	500 100	2/10 μ s 10/1000 μ s	5 2.5
GR-1089 Core Second level	5000	2/10 μ s	500	2/10 μ s	10
GR-1089 Core Intra-building	1500	2/10 μ s	100	2/10 μ s	0
ITU-T-K20/K21	6000 1500	10/700 μ s	150 37.5	5/310 μ s	10 0
ITU-T-K20 (IEC61000-4-2)	8000 15000	1/60 ns	ESD contact discharge ESD air discharge		0 0
VDE0433	4000 2000	10/700 μ s	100 50	5/310 μ s	0 0
VDE0878	4000 2000	1.2/50 μ s	100 50	1/20 μ s	0 0
IEC61000-4-5	4000 4000	10/700 μ s 1.2/50 μ s	100 100	5/310 μ s 8/20 μ s	0 0
FCC Part 68, lightning surge type A	1500 800	10/160 μ s 10/560 μ s	200 100	10/160 μ s 10/560 μ s	2.5 0
FCC Part 68, lightning surge type B	1000	9/720 μ s	25	5/320 μ s	0

Table 3: Absolute Ratings ($T_{amb} = 25^{\circ}\text{C}$)

Symbol	Parameter		Value	Unit
I_{PP}	Repetitive peak pulse current (see figure 2)	10/1000 μ s 8/20 μ s 10/560 μ s 5/310 μ s 10/160 μ s 1/20 μ s 2/10 μ s	80 200 100 120 150 200 250	A
I_{FS}	Fail-safe mode : maximum current (note 1)	8/20 μ s	5	kA
I_{TSM}	Non repetitive surge peak on-state current (sinusoidal)	t = 0.2 s t = 1 s t = 2 s t = 15 mn	14 8 6.5 2	A
I^2t	I^2t value for fusing	t = 16.6 ms t = 20 ms	7.5 7.8	A ² s
T_{stg} T_j	Storage temperature range Maximum junction temperature		-55 to 150 150	$^{\circ}\text{C}$
T_L	Maximum lead temperature for soldering during 10 s.		260	$^{\circ}\text{C}$

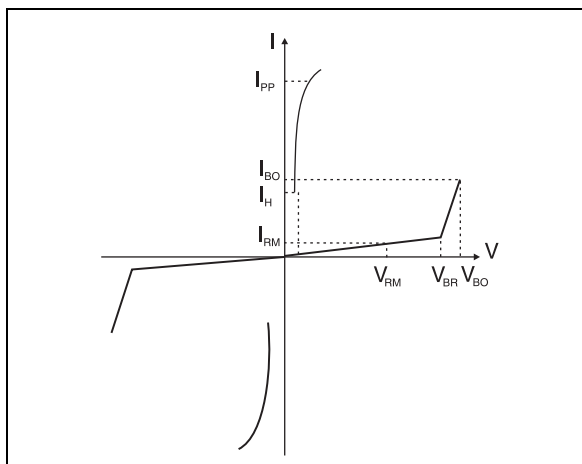
Note 1: in fail safe mode, the device acts as a short circuit

Table 4: Thermal Resistances

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Junction to ambient (with recommended footprint)	100	°C/W
$R_{th(j-l)}$	Junction to leads	20	°C/W

Table 5: Electrical Characteristics ($T_{amb} = 25^{\circ}\text{C}$)

Symbol	Parameter
V_{RM}	Stand-off voltage
V_{BR}	Breakdown voltage
V_{BO}	Breakover voltage
I_{RM}	Leakage current
I_{PP}	Peak pulse current
I_{BO}	Breakover current
I_H	Holding current
V_R	Continuous reverse voltage
I_R	Leakage current at V_R
C	Capacitance



Types	$I_{RM} @ V_{RM}$		$I_R @ V_R$		Dynamic V_{BO}	Static $V_{BO} @ I_{BO}$		I_H	C	C
	max.		max. note 1		max. note 2	max.	max.	min. note 4	typ. note 5	typ. note 6
	μA	V	μA	V	V	V	mA	mA	pF	pF
SMP80MC-120	2	108	5	120	155	155	800	150	12	25
SMP80MC-140		126		140	180	180				
SMP80MC-160		144		160	205	205				
SMP80MC-200		180		200	255	255				
SMP80MC-230		207		230	295	295				
SMP80MC-270		243		270	345	345				

Note 1: I_R measured at V_R guarantee $V_{BR} \min \geq V_R$

Note 2: see functional test circuit 1

Note 3: see test circuit 2

Note 4: see functional holding current test circuit 3

Note 5: $V_R = 50\text{V}$ bias, $V_{RMS}=1\text{V}$, $F=1\text{MHz}$

Note 6: $V_R = 2\text{V}$ bias, $V_{RMS}=1\text{V}$, $F=1\text{MHz}$

Figure 2: Pulse waveform

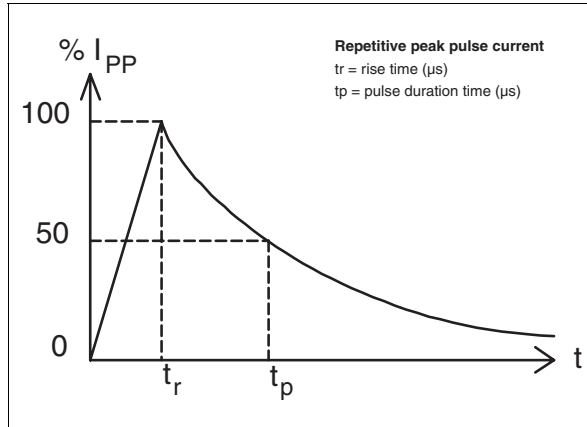


Figure 4: On-state voltage versus on-state current (typical values)

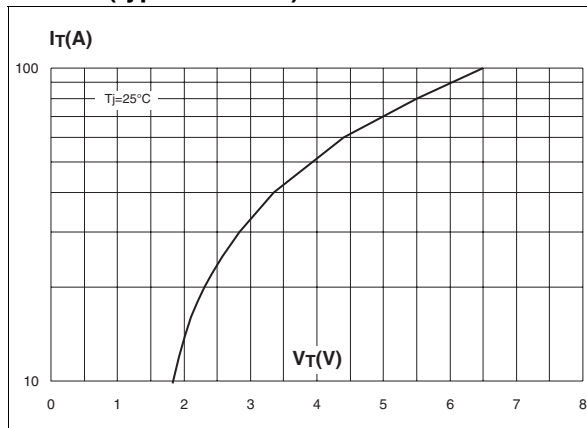


Figure 6: Relative variation of breakover voltage versus junction temperature

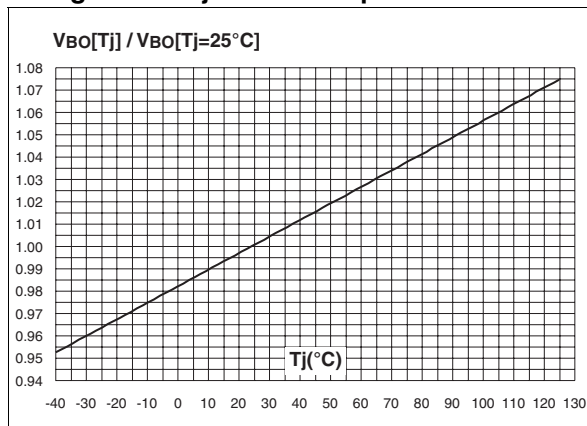


Figure 3: Non repetitive surge peak on-state current versus overload duration

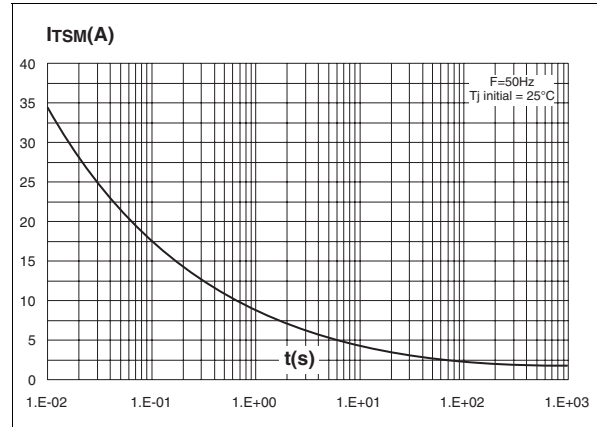


Figure 5: Relative variation of holding current versus junction temperature

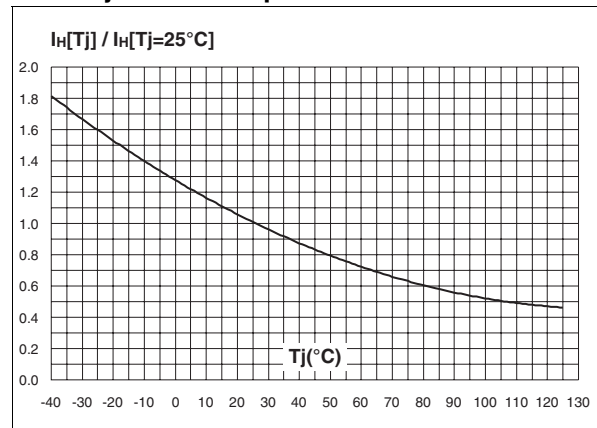


Figure 7: Relative variation of leakage current versus junction temperature (typical values)

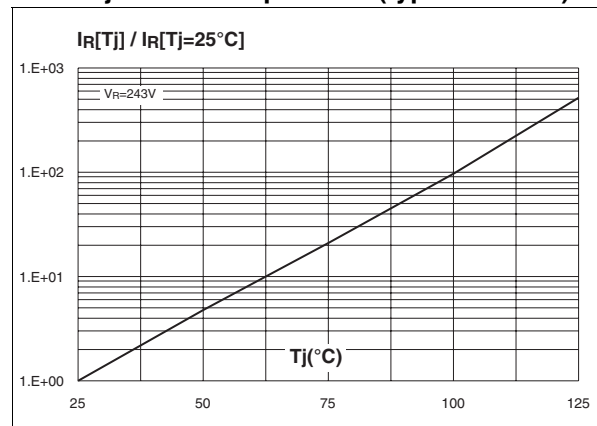


Figure 8: Variation of thermal impedance junction to ambient versus pulse duration (Printed circuit board FR4, SCu=35μm, recommended pad layout)

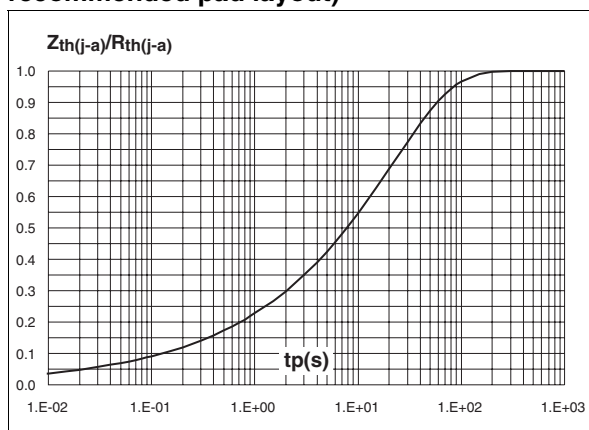


Figure 9: Relative variation of junction capacitance versus reverse voltage applied (typical values)

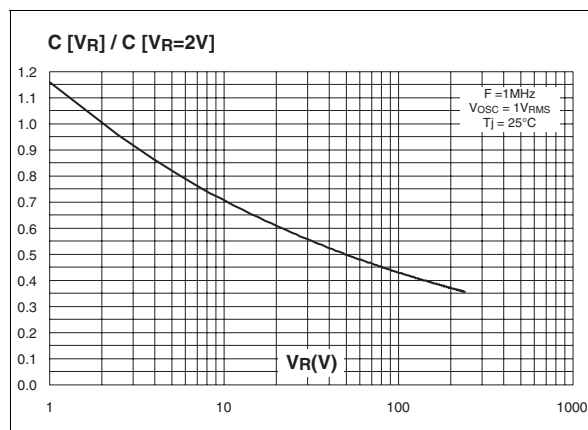


Figure 10: Test circuit 1 for dynamic I_{BO} and V_{BO} parameters

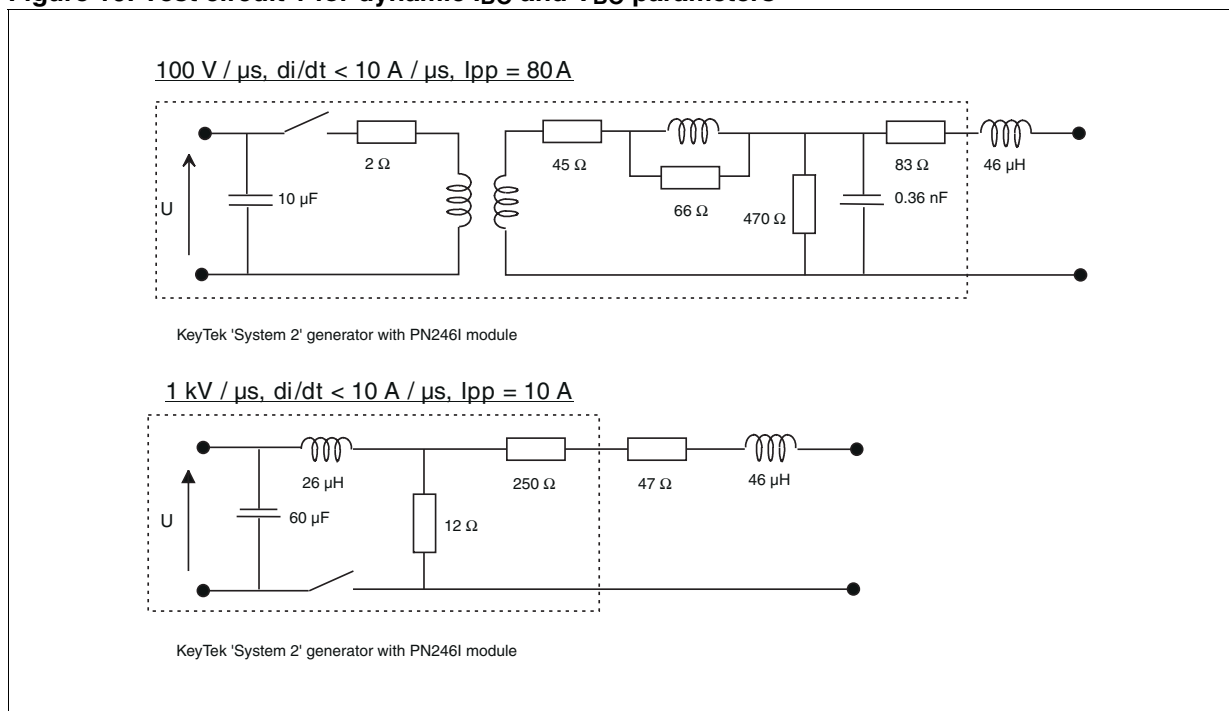


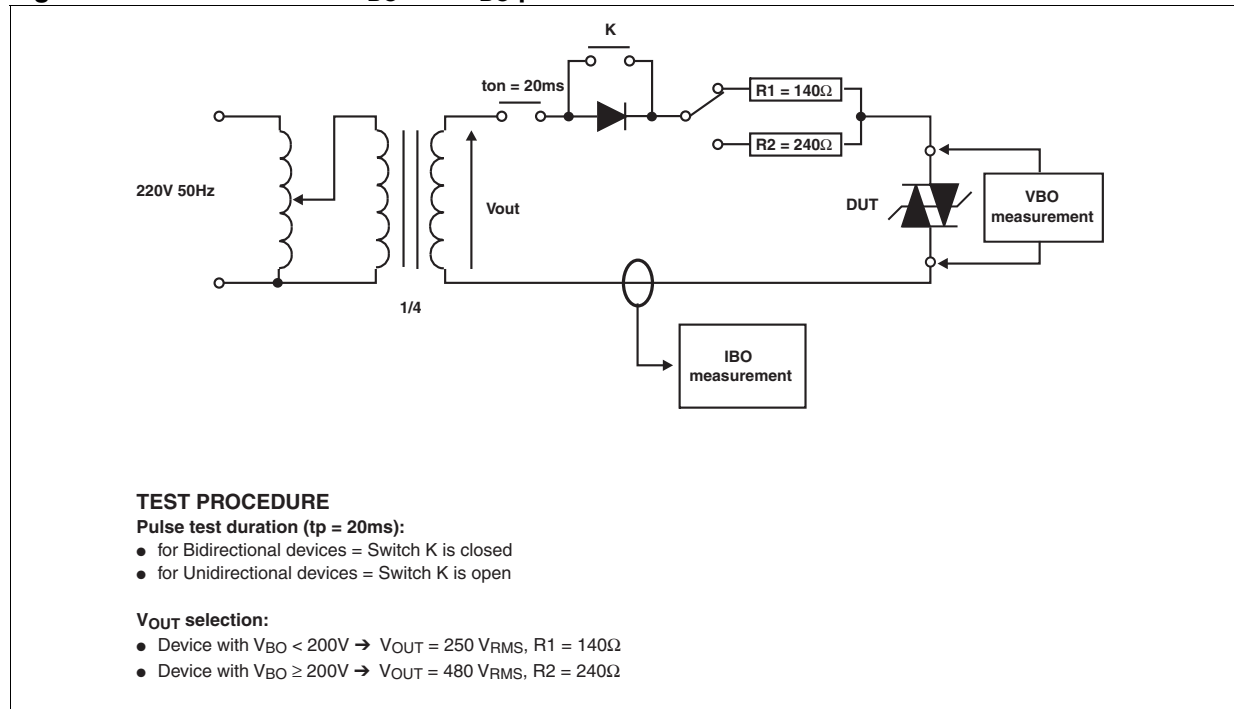
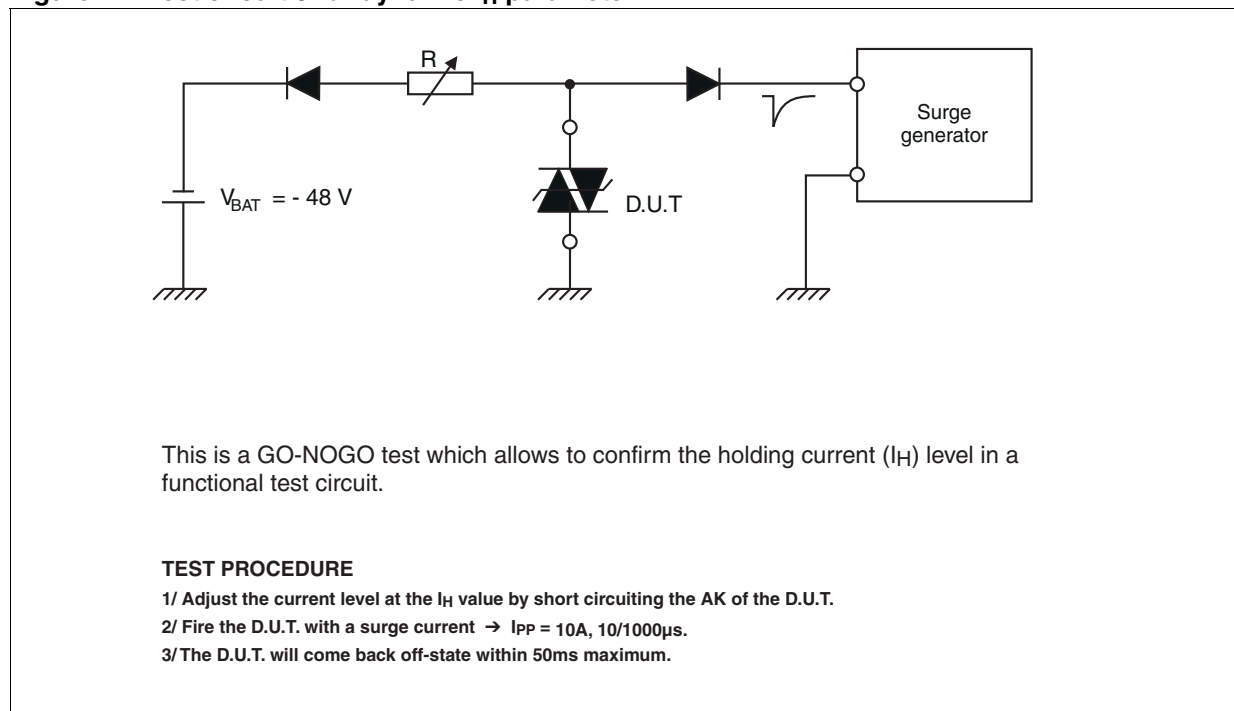
Figure 11: Test circuit 2 for I_{BO} and V_{BO} parametersFigure 12: Test circuit 3 for dynamic I_H parameter

Figure 13: Ordering Information Scheme

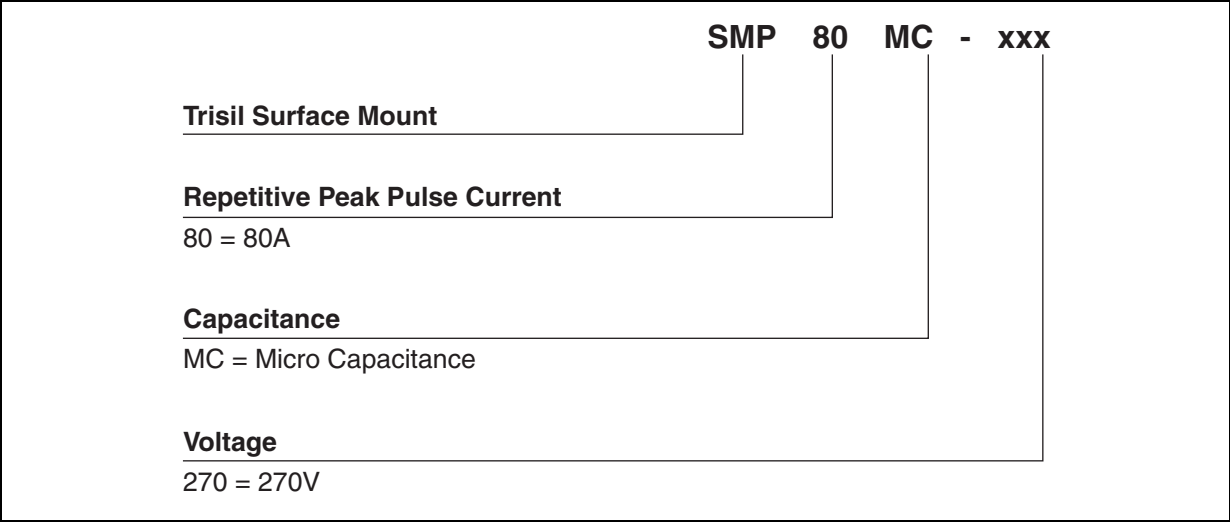


Figure 14: SMB Package Mechanical Data

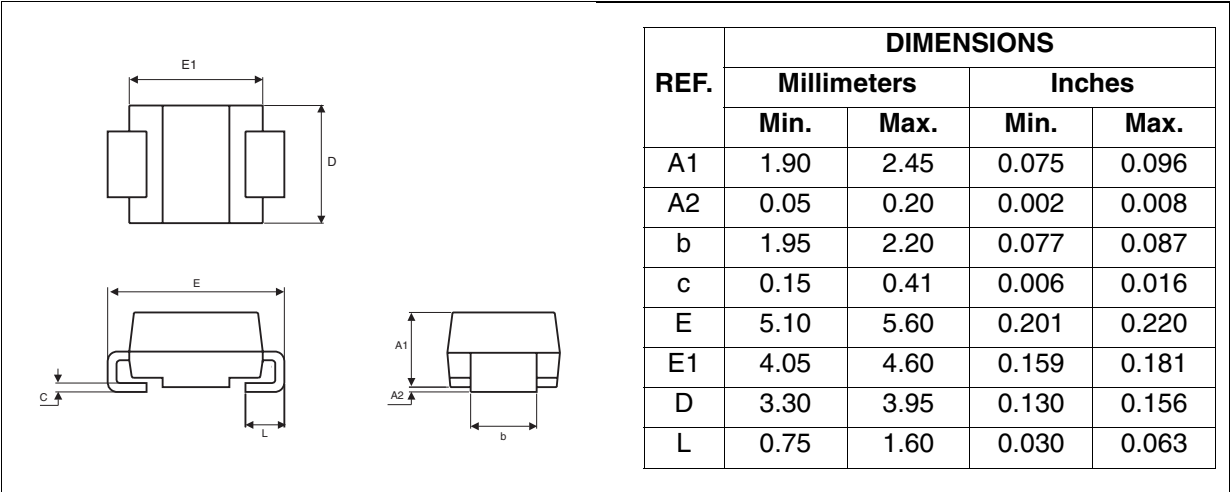
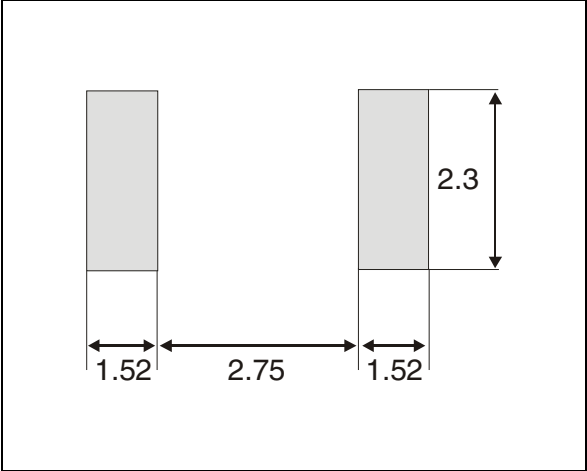


Figure 15: Foot Print Dimensions (in millimeters)



SMP80MC

Table 6: Ordering Information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
SMP80MC-120	TP12	SMB	0.11 g	2500	Tape & reel
SMP80MC-140	TP14				
SMP80MC-160	TP16				
SMP80MC-200	TP20				
SMP80MC-230	TP23				
SMP80MC-270	TP27				

Table 7: Revision History

Date	Revision	Description of Changes
September-2001	1	First issue.
11-May-2005	2	New types introduction.
20-Jun-2005	3	Qualification of new types

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